

WHAT IS CLAIMED IS:

1. A group III nitride compound semiconductor light-emitting device, comprising:

a semiconductor laminate portion including a
5 light-emitting layer; and
a reflection surface disposed so as to be opposite to
a side surface of said semiconductor laminate portion, wherein
said semiconductor laminate portion and said reflection surface
are provided in one and the same chip.

10 2. A group III nitride compound semiconductor light-emitting device according to claim 1, wherein said reflection surface reflects light from said side surface of said semiconductor laminate portion into a direction of an
15 optical axis of said light-emitting device.

3. A group III nitride compound semiconductor light-emitting device according to claim 1, wherein a distance
between said reflection surface and said side surface of said
20 semiconductor laminate portion is in a range of from 0.1 to
10 μm .

4. A group III nitride compound semiconductor light-emitting device according to claim 1, wherein said
25 reflection surface is made of a material which is the same as

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that of an n pad electrode .

5 5. A group III nitride compound semiconductor light-emitting device according to claim 4, wherein a portion of said n pad electrode opposite to said side surface of said semiconductor laminate portion forms a second reflection surface.

10 6. A group III nitride compound semiconductor light-emitting device according to claim 4, wherein said reflection surface is formed on an n-type semiconductor layer which is formed by etching to be a first depth, and said n pad electrode is formed on said n-type semiconductor layer which is formed by etching to be a second depth shallower than said
15 first depth.

20 7. A group III nitride compound semiconductor light-emitting device according to claim 4, wherein said reflection surface is formed integrally with said n pad electrode .

8. A group III nitride compound semiconductor light-emitting device, comprising:

25 a laminate of group III nitride compound semiconductor layers inclusive of a light-emitting layer;

a groove formed in said laminate; and
a reflection surface formed on an outer side surface of
said groove.

5 9. A group III nitride compound semiconductor
light-emitting device according to claim 8, wherein said groove
is formed by a dicing saw.

10 10. A group III nitride compound semiconductor
light-emitting device according to claim 8, wherein said
reflection surface is made of a metal layer.

15 11. A group III nitride compound semiconductor
light-emitting device according to claim 10, wherein said metal
layer is made of a material which is the same as that of an
n pad electrode , and said metal layer is formed at the same
time when said n pad electrode is formed.

20 12. A group III nitride compound semiconductor
light-emitting device according to claim 8, wherein light
emitted from a side surface of said laminate is reflected by
said reflected surface in a direction of an optical axis of
said light-emitting device.

25 13. A group III nitride compound semiconductor

light-emitting device according to claim 8, wherein said groove has a depth to reach a substrate.

14. A group III nitride compound semiconductor
5 light-emitting device according to claim 8, wherein said groove is substantially parallel to a chip cutting line.

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